NSN 5962-01-373-5206

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View Online at https://aerobasegroup.com/nsn/5962-01-373-5206

Body	Length:
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Between 1.260 inches and 1.280 inches

Body Width:

Between 0.290 inches and 0.310 inches

Body Height:

Between 0.180 inches and 0.200 inches

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Eo lorops

Features Provided:

Burn in and compatible cmos and erasable and electrostatic sensitive and programmed and hermetically sealed and w/clock

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

22 input

Criticality Code Justification:

Feat

Case Outline Source And Designator:

D-9 mil-m-38510

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, programmed

Voltage Rating And Type Per Characteristic:

-2.0 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

55.00 nanoseconds propagation delay time, high to low level output and 55.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Pal

Special Features:

Electrostatic discharge sensitive; altered item, made from 5962-8686401la, programmed per 1058-u10.Jed, fd137200067-001, checksum 188f; nha pn 1372ae1058

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

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Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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